

# 2 Channel Power Management IC For Portable Devices

## **GENERAL DESCRIPTION**

The EMQ9920 is a high efficiency, 2-channel power management IC for battery-powered, portable devices application. It integrates two high efficiency step-down DC/DC converters.

The two Synchronous Buck converters (CH3, CH4) operate from 2.5V to 5.5V input voltage, up to 600mA loading capability and regulate adjustable output voltage from 0.6V to 5.5V. It features low quiescent current, 1.5MHz internal frequency operation.

The EMQ9920 is available in TQFN16 3x3 package. It is **Green compliant** (RoHS and Halogen-free).

## **FEATURES**

#### Two Synchronous Buck Converters

- · Achieve 95% efficiency
- Input Voltage: 2.5V to 5.5V
- Output Current up to 600mA
- Reference voltage 0.6V
- Quiescent Current 200  $\mu$  A with No Load
- Internal switching frequency 1.5MHz
- No Schottky Diode needed
- · Low Dropout Operation: 100% Duty Cycle
- Shutdown current < 1  $\mu$  A
- Excellent Line and Load Transient Response
- · Over-temperature Protection

## **APPLICATIONS**

- · Blue-Tooth devices
- · Cellular and Smart Phones
- Personal multi-media Player (PMP)
- Wireless networking
- Digital Still Cameras
- Portable applications

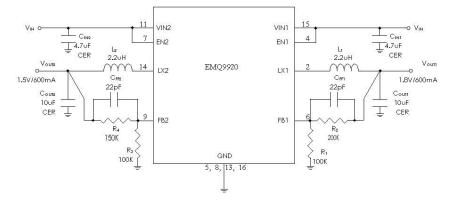
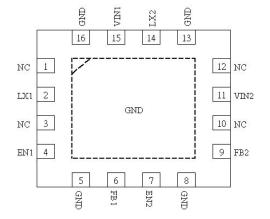


Figure 1. Typical Application



# **CONNECTION DIAGRAM**

# TQFN16 3x3



# **ORDER INFORMATION**

#### EMQ9920-00HB16NRR

00 Adjustable output voltage

HB16 TQFN16 Package

N Green(RoHS and Halogen-free)

R Commercial Grade Temperature

Rating: -40 to 85°C

R Package in Tape & Reel

# **MARKING & PACKING INFORMATION**

Package	Product ID	Marking	Packing
TQFN16	EMQ9920-00HB16NRR	EMP EMQ9920 Tracking Code	5K units Tape & Reel

# **TERMINAL FUNCTIONS**

TERMINAL		1/0	DESCRIPTION	
NAME	NO.	1/0	DESCRIPTION	
NC	1, 3, 10, 12	N/A	Non-connection.	
LX1	2	0	CH1 Switch PIN.	
			Must be connected to Inductor. This pin connects to the drains of the	
			internal main and synchronous power MOSFET switches.	
EN1	4	I	CH1 Enable Input.	
			Minimum 1.3V to enable the device. Maximum 0.5V to shut down the	
			device. Do not leave this pin floating and enable the chip after $V_{\text{IN}\text{I}}$ is	
			in the input voltage range.	
GND	5, 8, 13, 16	I	Ground PIN.	
FB1	6	I	CH1 Voltage Feedback PIN.	

Publication Date: Mar. 2009 Revision: 2.0 2/18

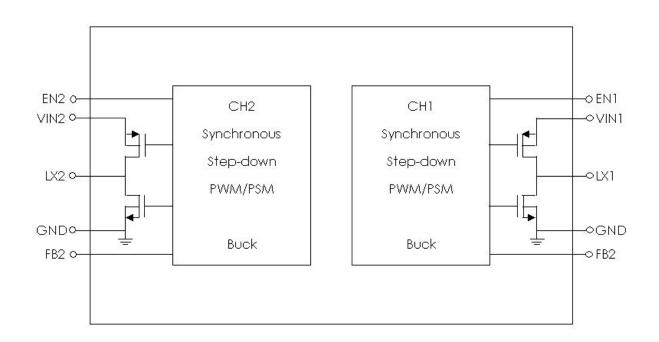


			Receives the feedback voltage from an external resistive divider	
			across the output Vouti.	
EN2	7	I	CH2 Enable Input.	
			Minimum 1.3V to enable the device. Maximum 0.5V to shut down the	
			device. Do not leave this pin floating and enable the chip after $V_{\text{IN2}}$ is	
			in the input voltage range.	
FB2	9	I	CH2 Voltage Feedback PIN.	
			Receives the feedback voltage from an external resistive divider	
			across the output Vouti.	
VIN2	11	I	CH2 Input Voltage.	
			Must be closely decoupled to GND pin with a 4.7µF or greater ceramic	
			capacitor.	
LX2	14	0	CH2 Switch PIN.	
			Must be connected to Inductor. This pin connects to the drains of the	
			internal main and synchronous power MOSFET switches.	
VIN1	15	I	CH1 Input Voltage.	
			Must be closely decoupled to GND pin with a 4.7µF or greater ceramic	
			capacitor.	

# **FUNCTION BLOCK DIAGRAM**

Publication Date: Mar. 2009 Revision: 2.0 3/18

# **ESMT/EMP**





## **ABSOLUTE MAXIMUM RATINGS**

Supply Input Voltage -0.3V to 6.0V ESD Susceptibility TBD (VIN1, VIN2) Junction Temperature 150°C

LX1 Switch PIN Voltage -0.3V to (VIN1+0.3V) Thermal Resistance

**LX2 Switch PIN Voltage** -0.3V to (VIN2+0.3V)  $\theta_{JA}$  (TQFN16 3x3) 55°C/W

Other I/O PIN Voltage -0.3V to VIN (VN1, VIN2) Operating Ratings

Storage Temperature-65°C to +150°CTemperature Range-40°C  $\leq$  TA  $\leq$  85°CSwitch Source Current (DC)800mASupply Voltage $2.5V \leq V_{DD} \leq 5.5V$ 

Switch Sink Current (DC) 800mA (VIN1, VIN2)

## **ELECTRICAL CHARACTERISTICS**

Apply for  $V_{IN1}$  = 3.6V,  $V_{IN2}$  = 3.6V and  $T_A$  = 25°C (unless otherwise noted), Boldface limits apply for the operating

temperature extremes: -40°C and 85°C.

Symbol	Parameter	Conditions	EMQ9920			Units	
Symbol	Parameter	Conditions	Min	Тур	Max	UTIILS	
CH1 (Note	4)						
I <sub>VFB1</sub>	Feedback Current				±30	nA	
$V_{\text{FB1}}$	Regulated Feedback Voltage	T <sub>A</sub> = 25°C	0.588	0.600	0.612	· v	
<b>V</b> FB1	kegulatea reeaback voltage	-40°C ≤ T <sub>A</sub> ≤ 85°C	0.585	0.600	0.615		
$\Delta V_{\text{FB1}}$	Reference Voltage Line Regulation	V <sub>IN1</sub> = 2.5V to 5.5V			0.4	%/V	
$\Delta V_{\text{OVL1}}$	Output Over-voltage Lockout	$\Delta V_{OVL1} = V_{OVL1} - V_{FB1}$	20	50	80	mV	
	Output Voltage Line Regulation	V <sub>IN1</sub> = 2.5V to 5.5V			0.4	%/V	
$\Delta  V_OUT1$	Output Voltage Load Regulation			0.5		%	
I <sub>PK1</sub>	Peak Inductor Current	V <sub>IN1</sub> = 3V, V <sub>FB1</sub> = 0.5V or V <sub>OUT1</sub> = 90%, Duty Cycle < 35%		1.0		Α	
	Quiescent Current (Note 5)	$V_{FB1} = 0.5V \text{ or } V_{OUT1} = 90\%$		200	340	μΑ	
I <sub>Q1</sub>	Shutdown	V <sub>EN1</sub> = 0V, V <sub>IN1</sub> = 4.2V		0.1	1	μΑ	
	Oscillator Frequency	V <sub>FB1</sub> = 0.6V or V <sub>OUT1</sub> = 100%	1.2	1.5	1.8	MHz	
f <sub>OSC1</sub>	Oscillator frequency	$V_{FB1} = 0V \text{ or } V_{OUT1} = 0V$		290		kHz	
R <sub>PFET1</sub>	R DS(ON) of PMOS	$I_{LX1} = 100 \text{mA}$		0.45	0.55	Ω	
RNFET1	R DS(ON) of NMOS	$I_{LX1} = -100 \text{mA}$		0.40	0.5	Ω	
I <sub>LX1</sub>	LX1 Leakage	$V_{EN1} = 0V$ , $V_{LX1} = 0V$ or $5V$ , $V_{IN1} = 5V$			±1	μΑ	
V <sub>EN1</sub>	EN1 Threshold		0.5		1.3	٧	
l <sub>EN1</sub>	EN1 Leakage Current				±1	μΑ	
CH2 (Note	:4)			•			

Publication Date: Mar. 2009 Revision: 2.0 5/18



I <sub>VFB2</sub>	Feedback Current				±30	nA	
		T <sub>A</sub> = 25°C	0.588	0.600	0.612		
$V_{FB2}$	Regulated Feedback Voltage	-40°C ≤ T <sub>A</sub> ≤ 85°C	0.585	0.600	0.615	V	
$\Delta V_{FB2}$	Reference Voltage Line Regulation	V <sub>IN2</sub> = 2.5V to 5.5V			0.4	%/V	
$\Delta V_{\text{OVL2}}$	Output Over-voltage Lockout	$\Delta V_{OVL2} = V_{OVL2} - V_{FB2}$	20	50	80	mV	
	Output Voltage Line Regulation	V <sub>IN2</sub> = 2.5V to 5.5V			0.4	%/V	
$\Delta V_{\text{OUT2}}$ Output Voltage Load Regulation				0.5		%	
I <sub>PK2</sub>	Peak Inductor Current	$V_{IN2} = 3V$ , $V_{FB2} = 0.5V$ or $V_{OUT2} = 90\%$ , Duty Cycle < 35%		1.0		Α	
	Quiescent Current (Note 5)	$V_{FB2} = 0.5V \text{ or } V_{OUT2} = 90\%$		200	340	μΑ	
I <sub>Q2</sub>	Shutdown	V <sub>EN2</sub> = 0V, V <sub>IN2</sub> = 4.2V		0.1	1	μΑ	
		V <sub>FB2</sub> = 0.6V or V <sub>OUT2</sub> = 100%	1.2	1.5	1.8	MHz	
fosc2	Oscillator Frequency	V <sub>FB2</sub> = 0V or V <sub>OUT2</sub> = 0V		290		kHz	
R <sub>PFET2</sub>	R <sub>DS(ON)</sub> of PMOS	I <sub>LX2</sub> = 100mA		0.45	0.55	Ω	
R <sub>NFET2</sub>	R DS(ON) of NMOS	$I_{LX2} = -100 \text{mA}$		0.40	0.5	Ω	
I <sub>LX2</sub>	LX2 Leakage	$V_{EN2} = 0V$ , $V_{LX2} = 0V$ or $5V$ , $V_{IN2} = 5V$			±1	μΑ	
V <sub>EN2</sub>	EN2Threshold		0.5		1.3	٧	
I <sub>EN2</sub>	EN2 Leakage Current				±1	μΑ	

Note 1: Absolute Maximum ratings indicate limits beyond which damage may occur. Electrical specifications do not apply when operating the device outside of its rated operating conditions.

Note 2: All voltages are with respect to the potential at the ground pin.

Note 3: Maximum Power dissipation for the device is calculated using the following equations:

PD = 
$$\frac{T_{J(MAX)} - T_{A}}{\theta_{JA}}$$

where TJ(MAX) is the maximum junction temperature, TA is the ambient temperature, and  $\theta_{JA}$  is the junction-to-ambient thermal resistance.

Note 4: Build-in internal over-temperature protection to prevent over-load condition.

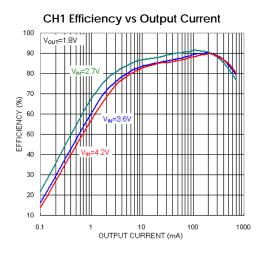
**Note 5:** Dynamic quiescent current is higher due to the gate charge being delivered at the switching frequency.

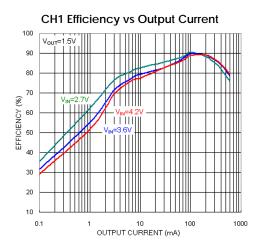
Publication Date: Mar. 2009 Revision: 2.0 6/18

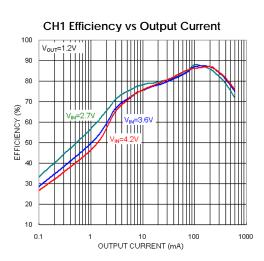


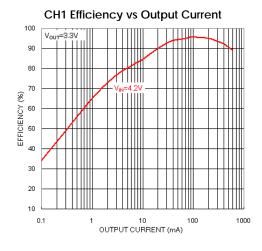
## TYPICAL PERFORMANCE CHARACTERISTICS

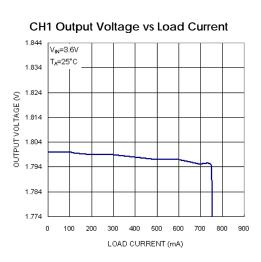
 $V_{EN1} = V_{IN1}, C_{IN1} = 4.7 \mu F, L_1 = 2.2 \mu H, C_{OUT1} = 4.7 \mu F, C_{IN2} = 4.7 \mu F, L_2 = 2.2 \mu H, C_{OUT2} = 4.7 \mu F, V_{EN2} = V_{IN2} T_A = 25 ^{\circ} C, unless otherwise specified the contraction of the contract$ 

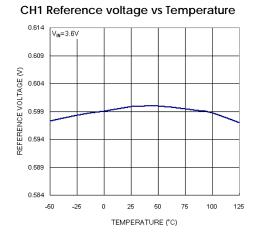




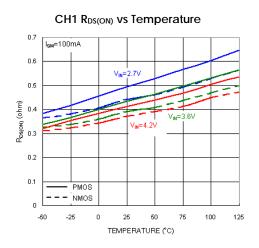


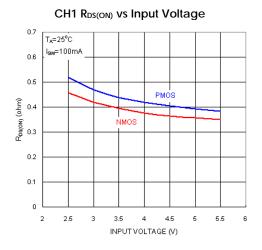




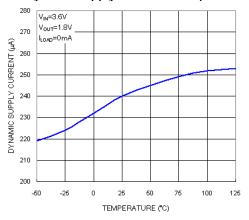


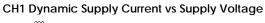


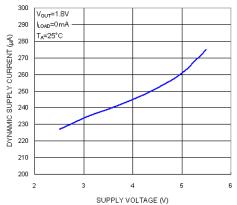




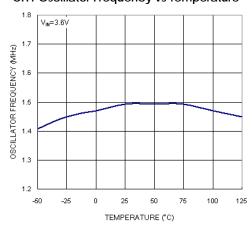
CH1 Dynamic Supply Current vs Temperature



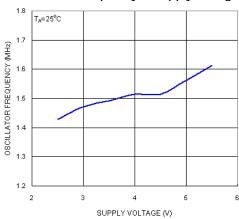




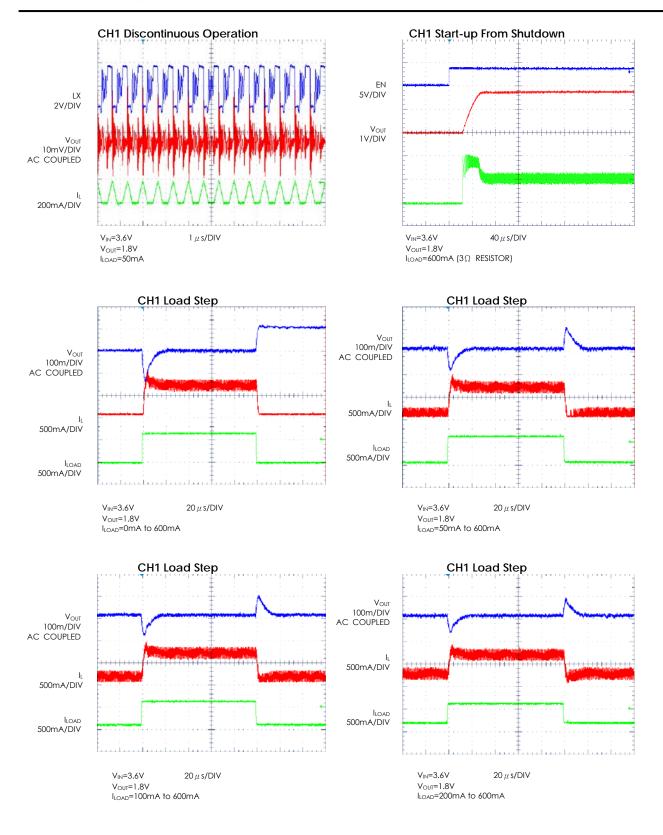
CH1 Oscillator Frequency vs Temperature



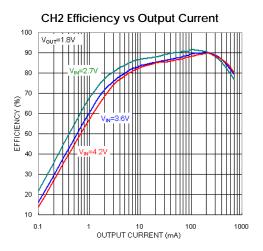
CH1 Oscillator Frequency vs Supply Voltage

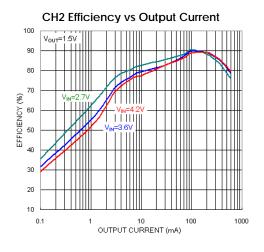


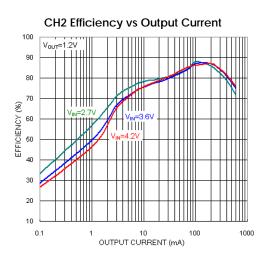


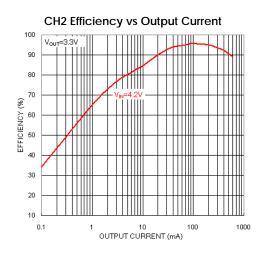


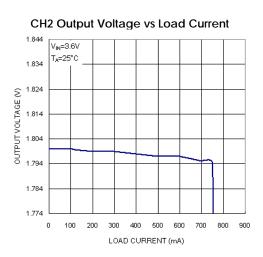


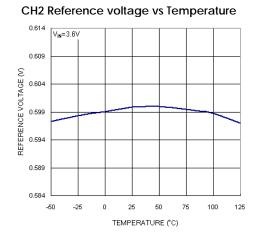




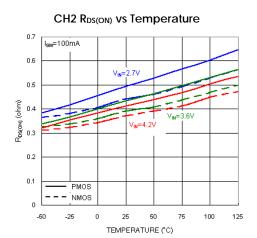


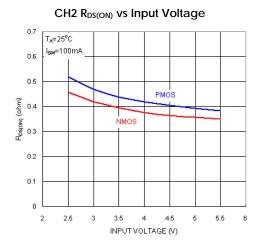




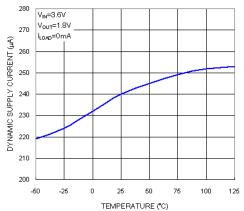




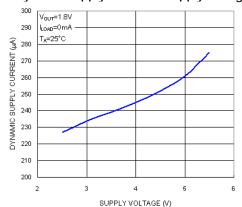




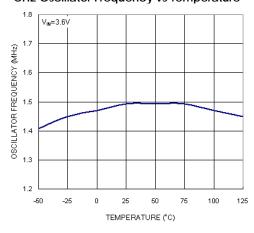
CH2 Dynamic Supply Current vs Temperature



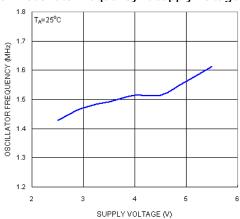
CH2 Dynamic Supply Current vs Supply Voltage



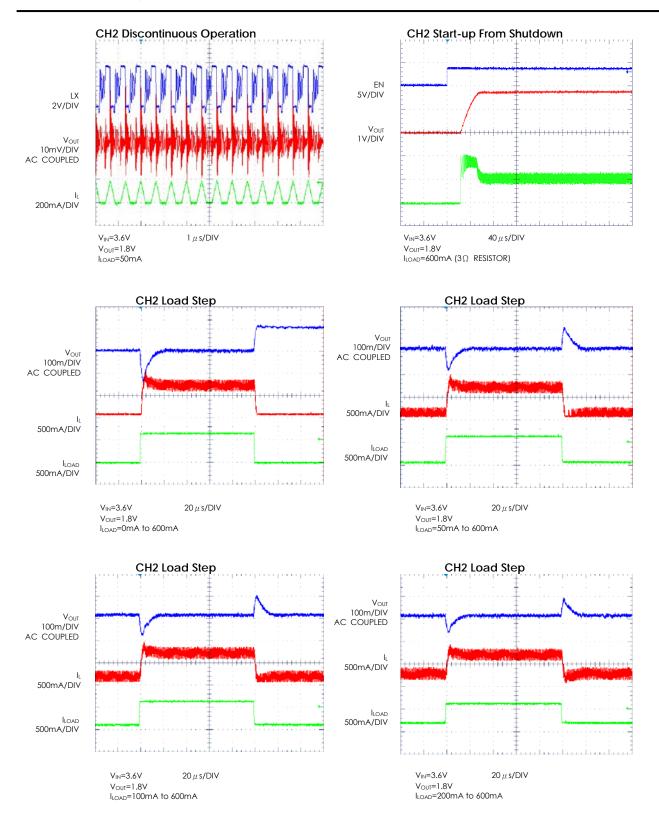
**CH2 Oscillator Frequency vs Temperature** 



CH2 Oscillator Frequency vs Supply Voltage







#### APPLICATION INFORMATION

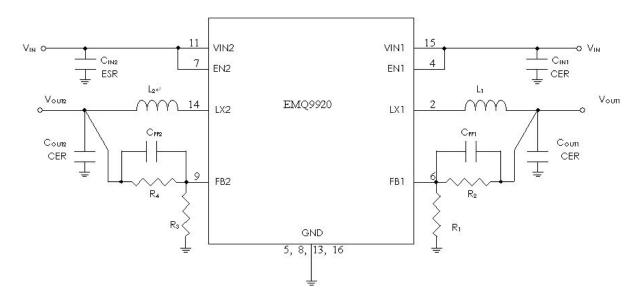


Figure 2. Typical EM9920 Application Circuit That Supports Two Adjustable Output Voltage



## **Application Information**

The EMQ9920 is a high efficiency, 2-channel power management IC for battery-powered, portable devices application.

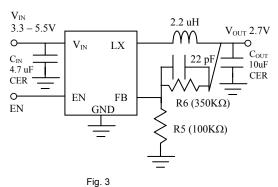
The two channels are listed as following:

#### CH1/2: 600mA Synchronous Buck converters

All 2 channels are Vout adjustable

#### CH1/2: 600mA Synchronous Buck converters

The typical application circuit of the current mode DC/DC converters is shown in Fig.3.



#### CH1, CH2 Inductor Selection

Basically, inductor ripple current and core saturation are two factors considered to decide the Inductor value.

$$\Delta I_{L} = \frac{1}{f \cdot L} V_{OUT} \left( 1 - \frac{V_{OUT}}{V_{IN}} \right) \dots (1)$$

The Eq. 1 shows the inductor ripple current is a function of frequency, inductance,  $VI_N$  ( $V_{IN1}$ ,  $V_{IN2}$ )

and  $V_{\text{OUT}}$  ( $V_{\text{OUT}}$ ),  $V_{\text{OUT}}$ ). It is recommended to set ripple current to 40% of max. load current. A low ESR inductor is preferred.

#### CH1, CH2 C<sub>IN</sub> and C<sub>OUT</sub> Selection

A low ESR input capacitor can prevent large voltage transients at  $VI_N$  ( $V_{IN1}$ ,  $V_{IN2}$ ). The RMS current of input capacitor is required larger than  $I_{RMS}$  calculated by:

$$I_{RMS} \cong I_{OMAX} \frac{\sqrt{V_{OUT}(V_{IN} - V_{OUT})}}{V_{IN}} \dots (2)$$

ESR is an important parameter to select  $C_{OUT}$  ( $C_{OUT1}$ ,  $C_{OUT2}$ ). The output ripple  $\triangle V_{OUT}$  ( $\triangle V_{OUT1}$ ,  $\triangle V_{OUT2}$ ) is determined by:

$$\Delta V_{OUT} \cong \Delta I_{L} \left( ESR + \frac{1}{8 \cdot f \cdot C_{OUT}} \right) \dots (3)$$

Higher values, lower cost ceramic capacitors are now available in smaller sizes. These ceramic capacitors have high ripple currents, high voltage ratings and low ESR that make them ideal for switching regulator applications. Optimize very low output ripple and small circuit size is doable from Cout selection since Cout does not affect the internal control loop stability. It is recommended to use the X5R or X7R which have the best temperature and voltage characteristics of all the ceramics for a given value and size.

#### CH1, CH2 Output Voltage (VOUT1, VOUT2)

The output voltage can be determined by following equation:

$$V_{OUT} = 0.6 V \left( 1 + \frac{R_2}{R_1} \right) \dots (4)$$

CH1 Case, Replace  $R_1$  as  $R_3$ ,  $R_2$  as  $R_4$  in CH2 case.

#### CH1, CH2 Thermal Considerations

Although thermal shutdown is build-in in the step-down DC/DC converter(s) that protects the device from thermal damage, the total power dissipation that the converter(s) can sustain should be base on the package thermal capability. The formula to ensure the safe operation is shown in Note 3.

To avoid the DC/DC converter(s) from exceeding the maximum junction temperature, the user will need to do some thermal analysis.

#### CH1, CH2 Guidelines for PCB Layout

To ensure proper operation of the DC/DC converter(s), please note the following PCB layout



guidelines:

1. The GND trace, the LX (LX1, LX2) trace and the  $V_{\text{IN}}$  (V<sub>IN1</sub>, V<sub>IN2</sub>) trace should be kept short, direct and wide.

2.  $V_{FB}$  (FB1, FB2) pin must be connected directly to the feedback resistors. Resistive divider  $R_1/R_2$  (CH1);  $R_3/R_4$  (CH2) must be connected and parallel to the output capacitor  $C_{OUT}$  ( $C_{OUT1}$ ,  $C_{OUT2}$ ).

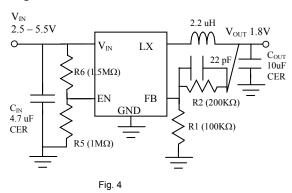
3. The Input capacitor  $C_{IN}$  ( $C_{IN1}$ ,  $C_{IN2}$ ) must be connected to pin  $V_{IN}$  ( $V_{IN1}$ ,  $V_{IN2}$ ) as closely as possible.

4. Keep LX (LX1, LX2) node away from the sensitive  $V_{\text{FB}}$  (FB1, FB2) node since this node is with high frequency and voltage swing.

5. Keep the (-) plates of C<sub>IN</sub> (C<sub>IN1</sub>, C<sub>IN2</sub>) and C<sub>OUT</sub> (C<sub>OUT1</sub>, C<sub>OUT2</sub>) as close as possible.

#### CH1, CH2 Self-Enable Application

A self-enable function could be used when the step-down DC/DC converter(s) is (are) connected as fig. 4.



The resistor ratio R5:R6=1:1.5 is recommended.

# CH1, CH2 Design Example

equation:

Assume the Step-down DC/DC converter(s) is (are) used in a single lithium-ion battery-powered application. The  $V_{\text{IN}}$  ( $V_{\text{IN1}}$ ,  $V_{\text{IN2}}$ ) range will be about 2.7V to 4.2V. Output voltage ( $V_{\text{OUT1}}$ ,  $V_{\text{OUT2}}$ ) is 1.8V. With this information we can calculate L using

$$L = \frac{1}{f \cdot \Delta I_{L}} V_{OUT} \left( 1 - \frac{V_{OUT}}{V_{IN}} \right)$$

Substituting  $V_{OUT}$  = 1.8V,  $V_{IN}$  = 4.2V,  $I_L$  = 240mA and f = 1.5MHz in eq. 1 gives:

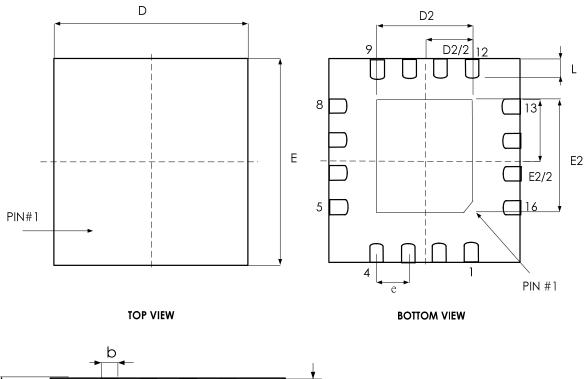
$$L = \frac{1.8V}{1.5 MHz \cdot 240 mA} \Biggl(1 - \frac{1.8V}{4.2V}\Biggr) = 2.86 \mu H$$

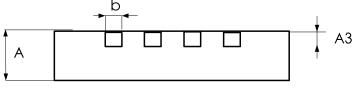
A 2.2µH inductor could be chose with thi application.

A greater inductor with less equivalent series resistance makes best efficiency.  $C_{\text{IN}}$  ( $C_{\text{IN1}}$ ,  $C_{\text{IN2}}$ ) will require an RMS current rating of at least  $I_{\text{LOAD}(\text{MAX})}/2$  and low ESR. In most cases, a ceramic capacitor will satisfy this requirement.



# **TQFN-16 OUTLINE DIMENSION**





**SIDE VIEW** 

	COMMON						
SYMBOL	DIMENSIONS MILLIMETER			DIMENSIONS INCH			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.700	0.750	0.800	0.027	0.029	0.031	
А3	0.195	0.203	0.211	0.0077	0.0080	0.0083	
b	0.180	0.230	0.300	0.007	0.009	0.012	
D	2.950	3.000	3.050	0.116	0.118	0.120	
Е	2.950	3.000	3.050	0.116	0.118	0.120	
е	0.50 BSC			0.020 BSC			
L	0.350	0.400	0.450	0.014	0.016	0.018	
D2	1.500	1.625	1.750	0.059	0.064	0.069	
E2	1.500	1.625	1.750	0.059	0.064	0.069	

<sup>©</sup> Copyright 2007 All rights reserved.



# **Revision History**

Revision	Date	Description
2.0	2009.03.18	EMP transferred from version 1.0

Publication Date: Mar. 2009 Revision: 2.0 17/18



# **Important Notice**

All rights reserved.

No part of this document may be reproduced or duplicated in any form or by any means without the prior permission of ESMT.

The contents contained in this document are believed to be accurate at the time of publication. ESMT assumes no responsibility for any error in this document, and reserves the right to change the products or specification in this document without notice.

The information contained herein is presented only as a guide or examples for the application of our products. No responsibility is assumed by ESMT for any infringement of patents, copyrights, or other intellectual property rights of third parties which may result from its use. No license, either express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of ESMT or others.

Any semiconductor devices may have inherently a certain rate of failure. To minimize risks associated with customer's application, adequate design and operating safeguards against injury, damage, or loss from such failure, should be provided by the customer when making application designs.

ESMT's products are not authorized for use in critical applications such as, but not limited to, life support devices or system, where failure or abnormal operation may directly affect human lives or cause physical injury or property damage. If products described here are to be used for such kinds of application, purchaser must do its own quality assurance testing appropriate to such applications.

Publication Date: Mar. 2009 Revision: 2.0 18/18